

## Product Summary

| $BV_{DSS}$ | $R_{DS(ON)}$                    | $I_D$<br>$T_C = +25^\circ C$ |
|------------|---------------------------------|------------------------------|
| -30V       | 3.8m $\Omega$ @ $V_{GS} = -10V$ | -135A                        |
|            | 6.0m $\Omega$ @ $V_{GS} = -5V$  | -110A                        |

## Description

This new generation MOSFET is designed to minimize  $R_{DS(ON)}$  and yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switch.

## Applications

- Switch

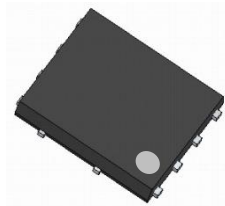
## Features

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low  $R_{DS(ON)}$  – Minimizes On State Losses
- <1.1mm Package Profile – Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**

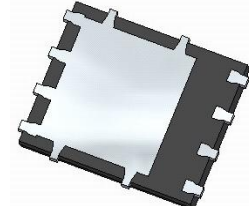
## Mechanical Data

- Case: PowerDI<sup>®</sup> 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208@3
- Weight: 0.097 grams (Approximate)

PowerDI5060-8

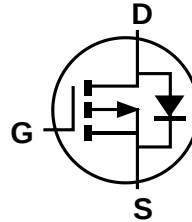


Top View

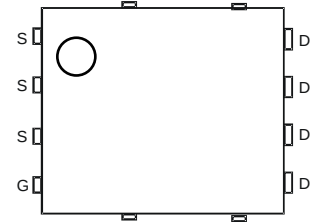


Bottom View

Pin1



Internal Schematic



Top View  
Pin Configuration

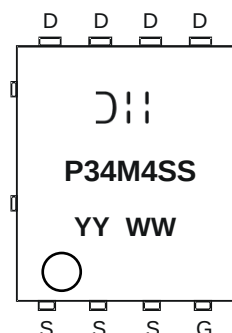
## Ordering Information (Note 4)

| Part Number   | Case          | Packaging           |
|---------------|---------------|---------------------|
| DMP34M4SPS-13 | PowerDI5060-8 | 2,500 / Tape & Reel |

- Notes:
- EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information

PowerDI5060-8



$\text{D} \parallel \parallel$  = Manufacturer's Marking  
 P34M4SS = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 18 = 2018)  
 WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                                   | Symbol           | Value                                            | Unit |
|------------------------------------------------------------------|------------------|--------------------------------------------------|------|
| Drain-Source Voltage                                             | V <sub>DSS</sub> | -30                                              | V    |
| Gate-Source Voltage                                              | V <sub>GSS</sub> | ±25                                              | V    |
| Continuous Drain Current, V <sub>GS</sub> = -10V (Note 7)        | I <sub>D</sub>   | T <sub>C</sub> = +25°C<br>T <sub>C</sub> = +70°C | A    |
|                                                                  |                  |                                                  |      |
| Continuous Drain Current, V <sub>GS</sub> = -10V (Note 6)        | I <sub>D</sub>   | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | A    |
|                                                                  |                  |                                                  |      |
| Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)              | I <sub>DM</sub>  | -350                                             | A    |
| Maximum Continuous Body Diode Forward Current (Note 6)           | I <sub>S</sub>   | -2.9                                             | A    |
| Pulsed Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%) | I <sub>SM</sub>  | -350                                             | A    |
| Avalanche Current, L = 0.1mH (Note 8)                            | I <sub>AS</sub>  | -60                                              | A    |
| Avalanche Energy, L = 0.1mH (Note 8)                             | E <sub>AS</sub>  | 180                                              | mJ   |

**Thermal Characteristics**

| Characteristic                                   | Symbol                            | Value       | Unit |
|--------------------------------------------------|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5)                 | P <sub>D</sub>                    | 1.5         | W    |
| Thermal Resistance, Junction to Ambient (Note 5) | R <sub>θJA</sub>                  | 94          | °C/W |
| Steady State                                     |                                   |             |      |
| Total Power Dissipation (Note 6)                 | P <sub>D</sub>                    | 3.0         | W    |
| Thermal Resistance, Junction to Ambient (Note 6) | R <sub>θJA</sub>                  | 47          | °C/W |
| Steady State                                     |                                   |             |      |
| Total Power Dissipation (Note 7)                 | P <sub>D</sub>                    | 100         | W    |
| Thermal Resistance, Junction to Case (Note 7)    | R <sub>θJC</sub>                  | 1.4         | °C/W |
| Operating and Storage Temperature Range          | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                           | Symbol              | Min  | Typ   | Max  | Unit | Test Condition                                                                                   |
|------------------------------------------|---------------------|------|-------|------|------|--------------------------------------------------------------------------------------------------|
| <b>OFF CHARACTERISTICS (Note 9)</b>      |                     |      |       |      |      |                                                                                                  |
| Drain-Source Breakdown Voltage           | BV <sub>DSS</sub>   | -30  | —     | —    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA                                                    |
| Zero Gate Voltage Drain Current          | I <sub>DSS</sub>    | —    | —     | -1   | µA   | V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V                                                     |
| Gate-Source Leakage                      | I <sub>GSS</sub>    | —    | —     | ±100 | nA   | V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V                                                     |
| <b>ON CHARACTERISTICS (Note 9)</b>       |                     |      |       |      |      |                                                                                                  |
| Gate Threshold Voltage                   | V <sub>GS(TH)</sub> | -1.6 | —     | -2.6 | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA                                      |
| Static Drain-Source On-Resistance        | R <sub>DS(ON)</sub> | —    | 2.9   | 3.8  | mΩ   | V <sub>GS</sub> = -10V, I <sub>D</sub> = -20A                                                    |
|                                          |                     | —    | 4.9   | 6.0  |      | V <sub>GS</sub> = -5V, I <sub>D</sub> = -20A                                                     |
| Diode Forward Voltage                    | V <sub>SD</sub>     | —    | -0.7  | -1.2 | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A                                                       |
| <b>DYNAMIC CHARACTERISTICS (Note 10)</b> |                     |      |       |      |      |                                                                                                  |
| Input Capacitance                        | C <sub>iss</sub>    | —    | 3,775 | —    | pF   | V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V<br>f = 1MHz                                         |
| Output Capacitance                       | C <sub>oss</sub>    | —    | 932   | —    | pF   |                                                                                                  |
| Reverse Transfer Capacitance             | C <sub>rss</sub>    | —    | 500   | —    | pF   |                                                                                                  |
| Gate Resistance                          | R <sub>g</sub>      | —    | 21    | —    | Ω    | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz                                             |
| Total Gate Charge                        | Q <sub>g</sub>      | —    | 127   | —    | nC   | V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V,<br>I <sub>D</sub> = -20A                         |
| Gate-Source Charge                       | Q <sub>gs</sub>     | —    | 24.5  | —    | nC   |                                                                                                  |
| Gate-Drain Charge                        | Q <sub>gd</sub>     | —    | 28.5  | —    | nC   |                                                                                                  |
| Turn-On Delay Time                       | t <sub>D(ON)</sub>  | —    | 6.9   | —    | ns   | V <sub>DD</sub> = -15V, V <sub>GEN</sub> = -10V,<br>R <sub>GEN</sub> = 3Ω, I <sub>D</sub> = -20A |
| Turn-On Rise Time                        | t <sub>r</sub>      | —    | 4.0   | —    | ns   |                                                                                                  |
| Turn-Off Delay Time                      | t <sub>D(OFF)</sub> | —    | 372   | —    | ns   |                                                                                                  |
| Turn-Off Fall Time                       | t <sub>f</sub>      | —    | 160   | —    | ns   | I <sub>F</sub> = -20A, di/dt = 500A/µs                                                           |
| Reverse Recovery Time                    | t <sub>rr</sub>     | —    | 26.5  | —    | ns   |                                                                                                  |
| Reverse Recovery Charge                  | Q <sub>rr</sub>     | —    | 37.3  | —    | nC   |                                                                                                  |

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

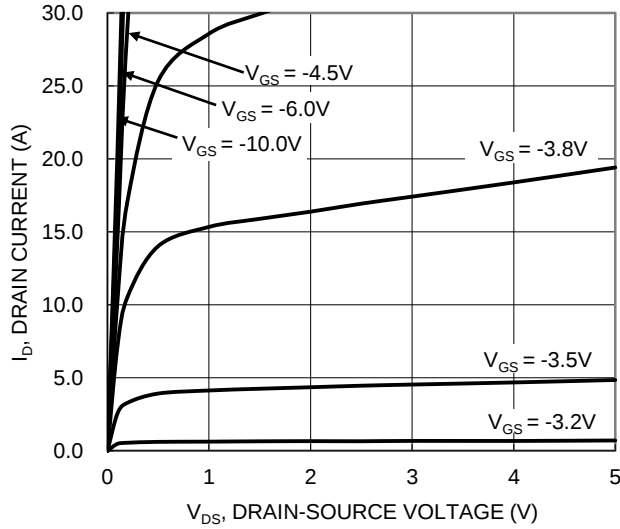


Figure 1. Typical Output Characteristic

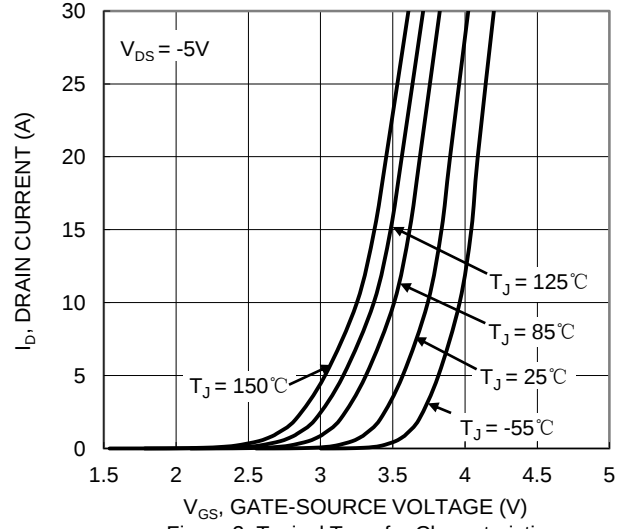


Figure 2. Typical Transfer Characteristic

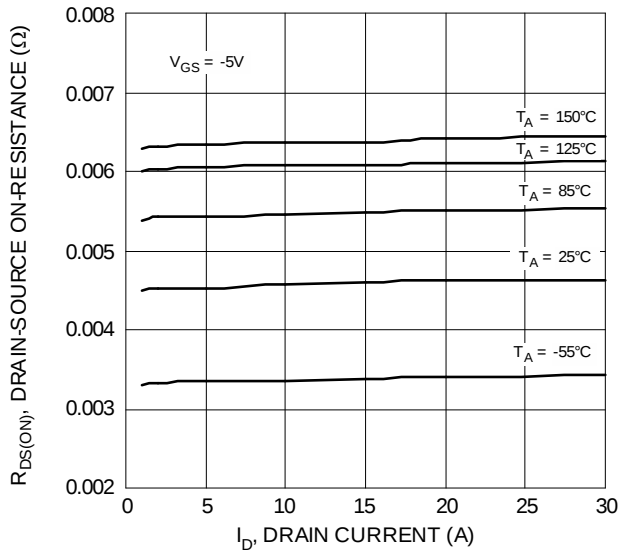


Figure 3 Typical On-Resistance vs. Drain Current and Junction Temperature

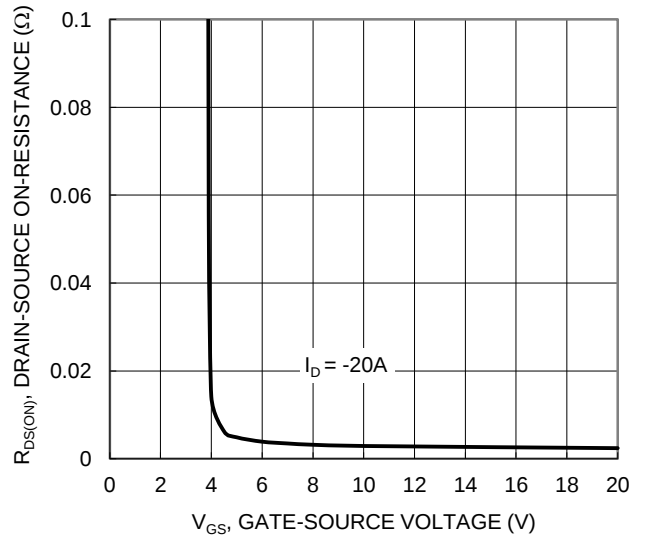


Figure 4. Typical Transfer Characteristic

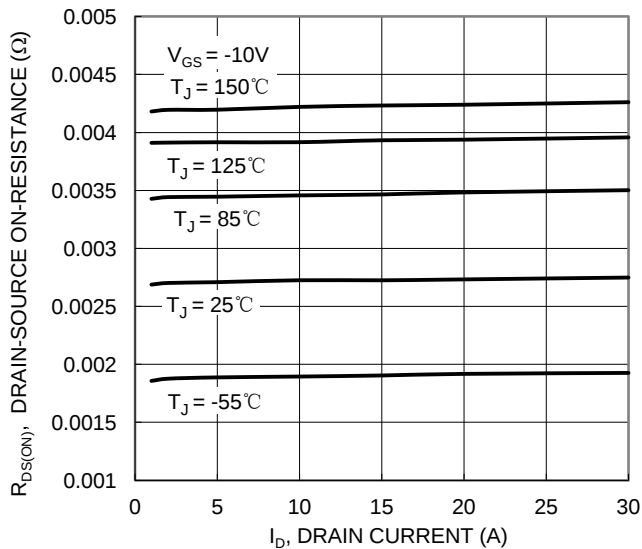


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

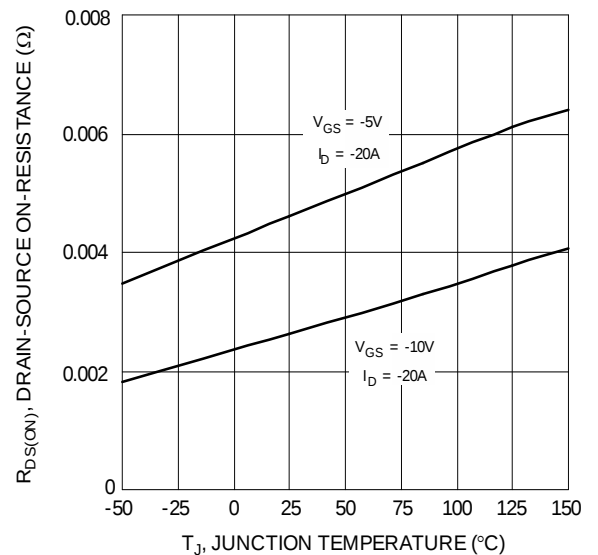


Figure 6 On-Resistance Variation with Junction Temperature

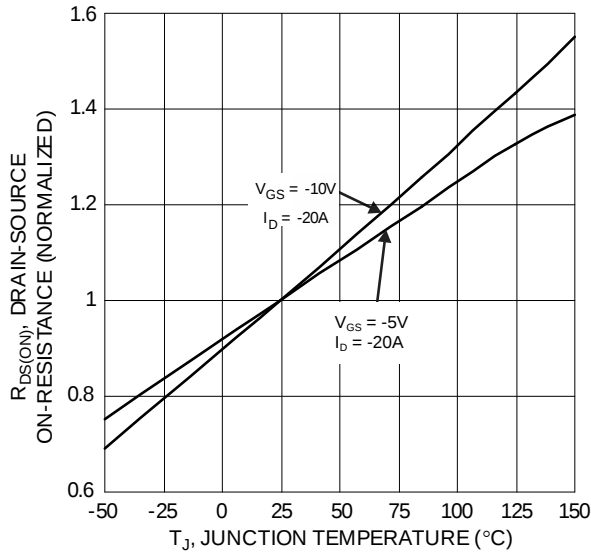


Figure 7 On-Resistance Variation with Junction Temperature

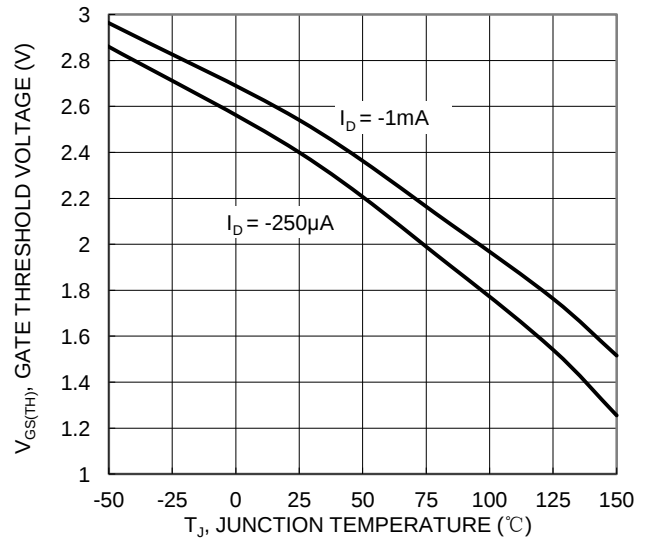


Figure 8. Gate Threshold Variation vs. Junction Temperature

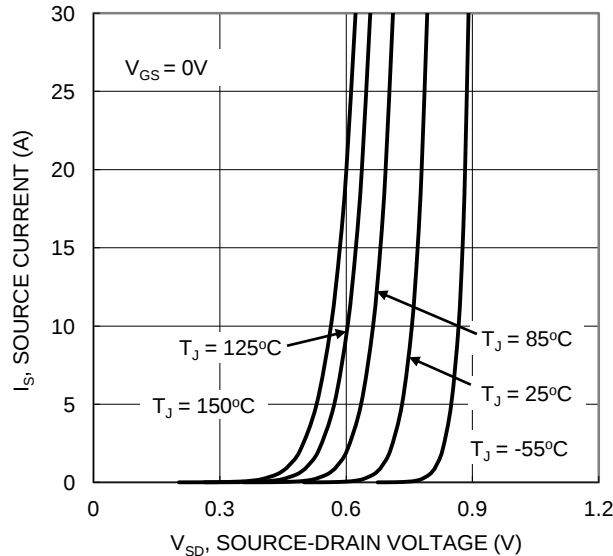


Figure 9. Diode Forward Voltage vs. Current

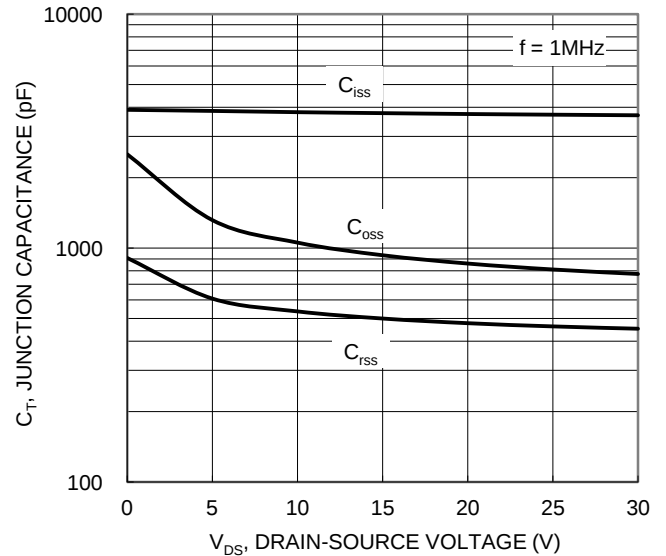


Figure 10. Typical Junction Capacitance

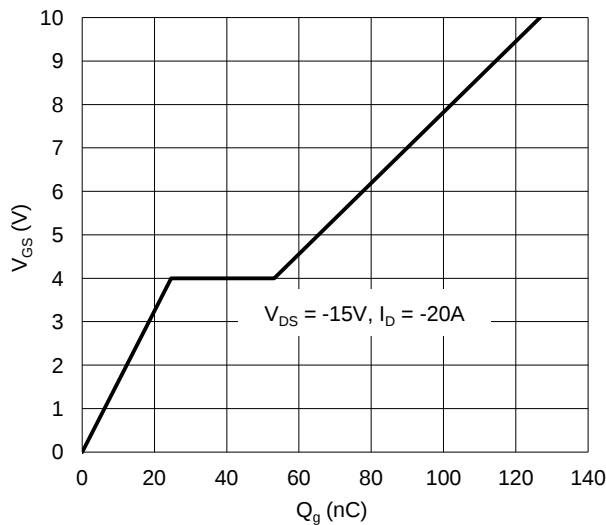


Figure 11. Gate Charge

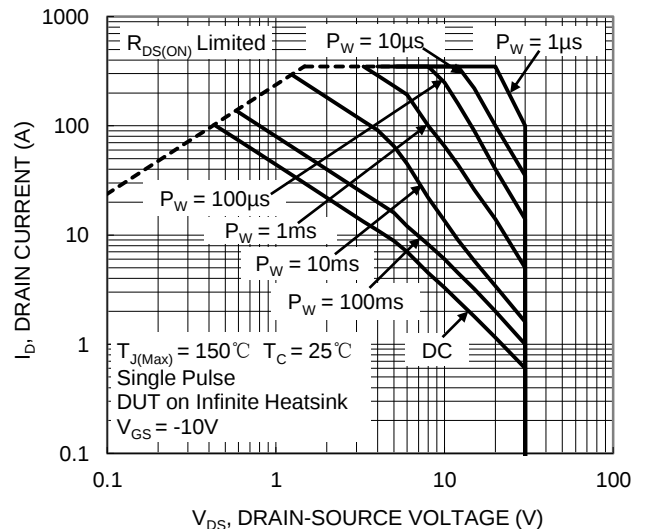


Figure 12. SOA, Safe Operation Area

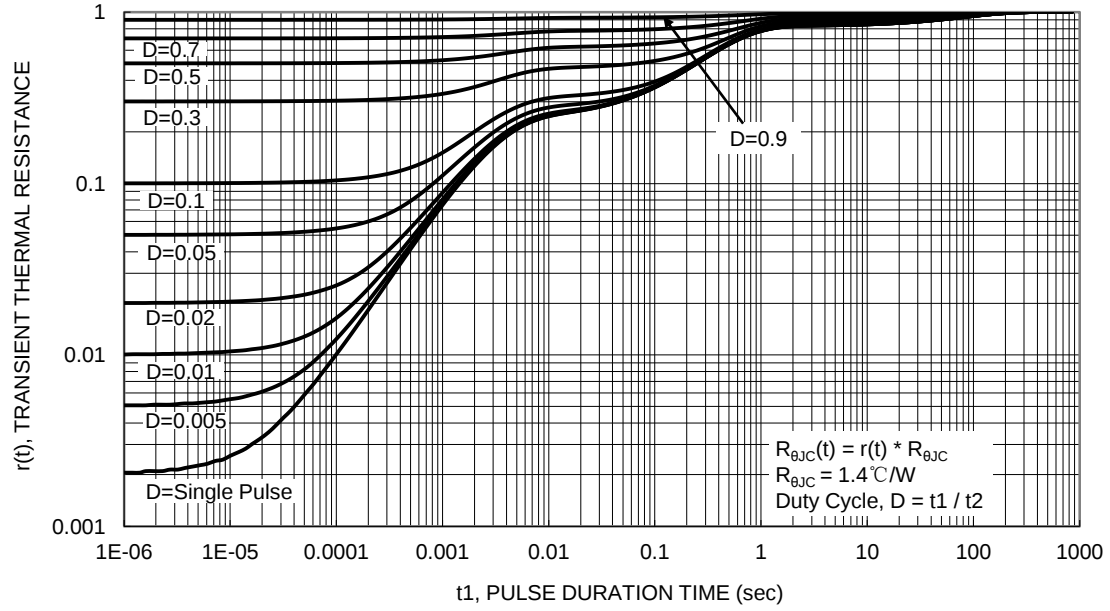
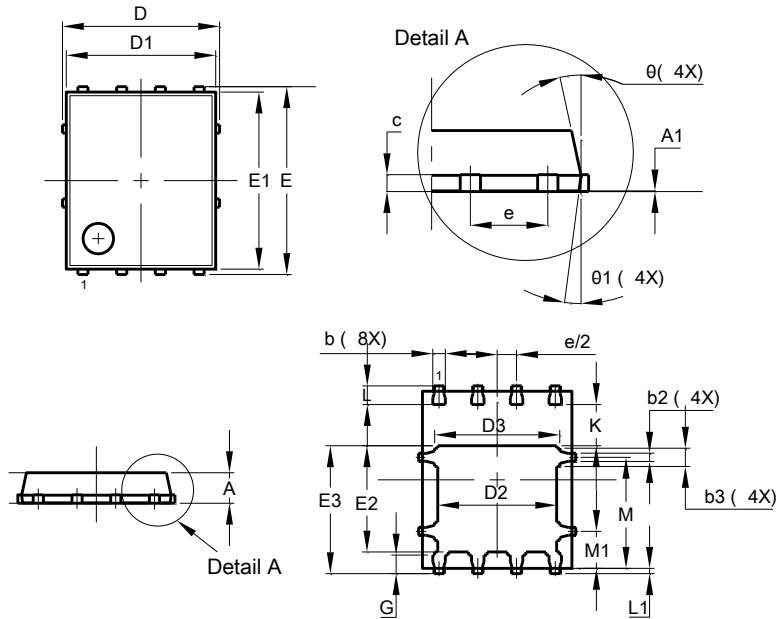


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### PowerDI5060-8

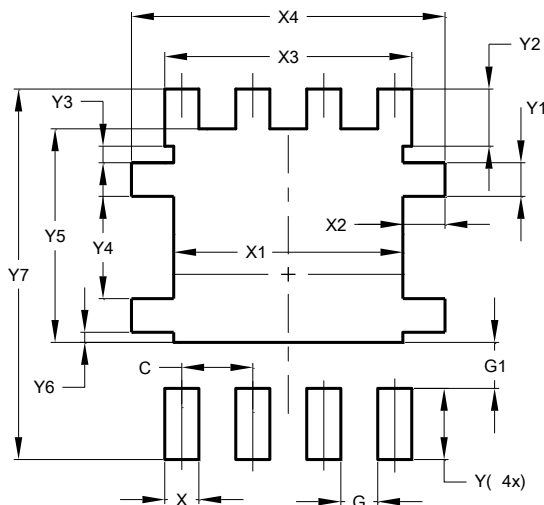


| PowerDI5060-8        |          |       |       |
|----------------------|----------|-------|-------|
| Dim                  | Min      | Max   | Typ   |
| A                    | 0.90     | 1.10  | 1.00  |
| A1                   | 0.00     | 0.05  | —     |
| b                    | 0.33     | 0.51  | 0.41  |
| b2                   | 0.200    | 0.350 | 0.273 |
| b3                   | 0.40     | 0.80  | 0.60  |
| c                    | 0.230    | 0.330 | 0.277 |
| D                    | 5.15 BSC |       |       |
| D1                   | 4.70     | 5.10  | 4.90  |
| D2                   | 3.70     | 4.10  | 3.90  |
| D3                   | 3.90     | 4.30  | 4.10  |
| E                    | 6.15 BSC |       |       |
| E1                   | 5.60     | 6.00  | 5.80  |
| E2                   | 3.28     | 3.68  | 3.48  |
| E3                   | 3.99     | 4.39  | 4.19  |
| e                    | 1.27 BSC |       |       |
| G                    | 0.51     | 0.71  | 0.61  |
| K                    | 0.51     | —     | —     |
| L                    | 0.51     | 0.71  | 0.61  |
| L1                   | 0.100    | 0.200 | 0.175 |
| M                    | 3.235    | 4.035 | 3.635 |
| M1                   | 1.00     | 1.40  | 1.21  |
| theta                | 10°      | 12°   | 11°   |
| theta1               | 6°       | 8°    | 7°    |
| All Dimensions in mm |          |       |       |

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### PowerDI5060-8



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 1.270         |
| G          | 0.660         |
| G1         | 0.820         |
| X          | 0.610         |
| X1         | 4.100         |
| X2         | 0.755         |
| X3         | 4.420         |
| X4         | 5.610         |
| Y          | 1.270         |
| Y1         | 0.600         |
| Y2         | 1.020         |
| Y3         | 0.295         |
| Y4         | 1.825         |
| Y5         | 3.810         |
| Y6         | 0.180         |
| Y7         | 6.610         |

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